

Taiwan Semiconductor

# 15A, 45V - 200V Schottky Barrier Rectifier

### FEATURES

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

## **MECHANICAL DATA**

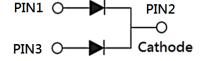
- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 1.88g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I <sub>F</sub>	15	А
V <sub>RRM</sub>	45 - 200	V
I <sub>FSM</sub>	150	А
T <sub>J MAX</sub>	150	°C
Package	TO-220AB	
Configuration	Dual d	lies





TO-220AB



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)							
		MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	1545	1560	15100	15150	15200	UNIT
		CT-Y	CT-Y	CT-Y	CT-Y	CT-Y	
Marking code on the device		MBR 1545CT	MBR 1560CT	MBR 15100CT	MBR 15150CT	MBR 15200CT	
Repetitive peak reverse voltage	$V_{RRM}$	45	60	100	150	200	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	31	42	70	105	140	V
Forward current	I <sub>F</sub>			15			Α
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>			150			Α
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1		C	).5		А
Peak repetitive forward current (Rated V <sub>R</sub> , Square wave, 20KHz)	I <sub>FRM</sub>			15			А
Critical rate of rise of off-state voltage	dv/dt			10,000			V/µs
Junction temperature	TJ			-55 to +1	50		°C
Storage temperature	T <sub>STG</sub>			-55 to +1	50		°C

Notes:

1. tp = 2.0µs, 1.0KHz



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-ambient thermal resistance	R <sub>eja</sub>	10	°C/W
Junction-to-case thermal resistance	R <sub>eJC</sub>	1.5	°C/W

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR1545CT-Y	I <sub>F</sub> = 7.5A, T <sub>J</sub> = 25°C		-	-	V
	MBR1560CT-Y			-	0.75	V
	MBR15100CT-Y			-	0.92	V
	MBR15150CT-Y MBR15200CT-Y			-	1.05	V
	MBR1545CT-Y			-	0.84	V
	MBR1560CT-Y			-	-	V
	MBR15100CT-Y	$I_F = 15A, T_J = 25^{\circ}C$		-	-	V
Forward voltage per	MBR15150CT-Y MBR15200CT-Y		- V <sub>F</sub>	-	-	V
diode <sup>(1)</sup>	MBR1545CT-Y	I <sub>F</sub> = 7.5A, T <sub>J</sub> = 125°C	VF	-	0.57	V
	MBR1560CT-Y			-	0.65	V
	MBR15100CT-Y		-	-	0.82	V
	MBR15150CT-Y MBR15200CT-Y			-	0.92	V
	MBR1545CT-Y	I <sub>F</sub> = 15A, T <sub>J</sub> = 125°C		-	0.72	V
	MBR1560CT-Y			-	-	V
	MBR15100CT-Y			-	-	V
	MBR15150CT-Y MBR15200CT-Y			-	-	V
	MBR1545CT-Y	т. 0500	- I <sub>R</sub> -	-	500	μA
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	MBR1560CT-Y			-	300	μA
	MBR15100CT-Y MBR15150CT-Y MBR15200CT-Y	T <sub>J</sub> = 25°C		-	100	μΑ
	MBR1545CT-Y			-	10	mA
	MBR1560CT-Y			-	7.5	mA
	MBR15100CT-Y MBR15150CT-Y MBR15200CT-Y	T <sub>J</sub> = 125°C		-	5	mA

## Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING
MBR15xCT-Y	TO-220AB	50 / Tube

#### Notes:

1. "x" defines voltage from 45V(MBR1545CT-Y) to 200V(MBR15200CT-Y)



# MBR1545CT-Y – MBR15200CT-Y

**Fig.2 Typical Junction Capacitance** 

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## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

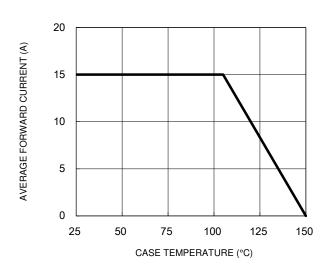
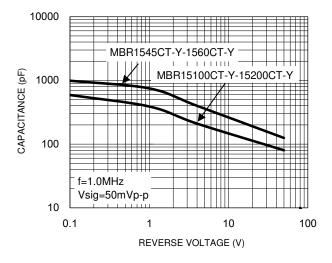
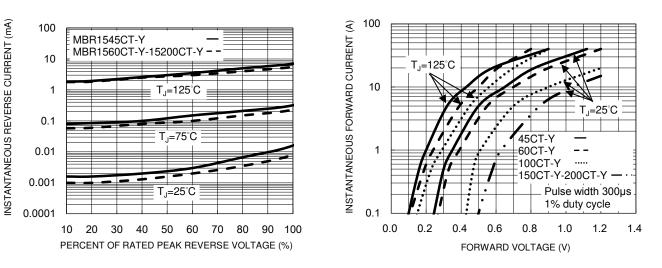


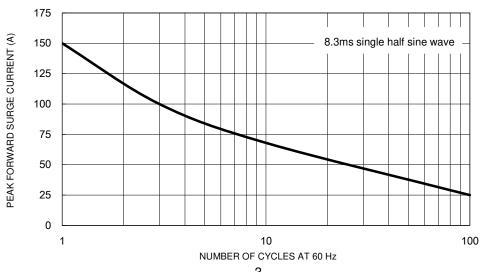
Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**



#### **Fig.4 Typical Forward Characteristics**





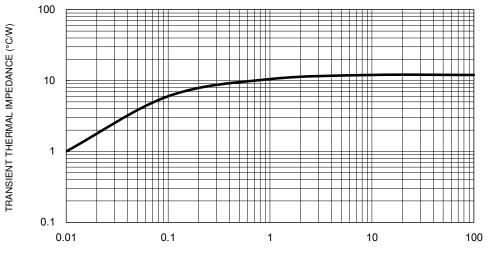
## Fig.5 Maximum Non-Repetitive Forward Surge Current

Version: D2104



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

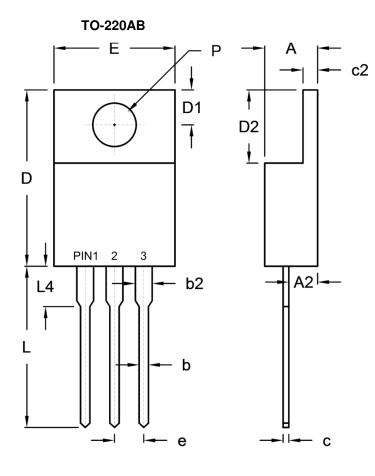


## Fig.6 Typical Transient Thermal Impedance

PULSE DURATION (s)

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## PACKAGE OUTLINE DIMENSIONS



DIM.	Unit (mm)		Unit	(inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
b2	1.14	1.77	0.045	0.070
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
L	13.19	14.79	0.519	0.582
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

## **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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